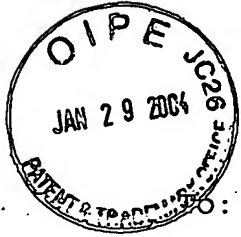


CS-99-065CCB



January 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/694,413 10/27/03

Paul Kwok Keung Ho et al.

PLASMA ETCH METHOD FOR FORMING
PLASMA ETCHED SILICON LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

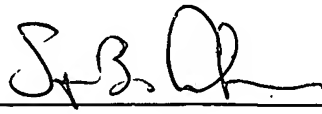
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

U.S. Patent 5,456,796 to Gupta et al., "Control of Particle Generation within a Reaction Chamber", discloses a plasma processing method for attenuating particulate generation and deposition upon a substrate employed within a microelectronic fabrication when processing the substrate employed within the microelectronic fabrication while employing the plasma processing method.

U.S. Patent 5,681,424 to Saito et al., "Plasma Processing Method", discloses a plasma etch method using HBr.

U.S. Patent 5,705,080 to Leung et al., "Plasma-Inert Cover and Plasma Cleaning Process", discloses a plasma cleaning process.

U.S. Patent 5,811,356 to Murugesu et al., "Reduction in Mobile Ion and Metal Contamination by Varying Season Time and Bias RF Power during Chamber Cleaning", teaches a season time variation during chamber clean.

U.S. Patent 5,431,772 to Babie et al., "Selective Silicon Nitride Plasma Etching Process," discloses a two step method of etching a silicon nitride layer carrying a surface oxygen film from a substrate in a plasma reactor.

U.S. Patent 5,824,375 to Gupta, "Decontamination of a Plasma Reactor using a Plasma after a Chamber Clean", discloses a plasma processing method and a plasma processing apparatus for reducing fluorine and other sorbable contaminants in a plasma reactor chamber employed within a chemical vapor deposition (CVD) method, such as but not limited to a plasma enhanced chemical vapor deposition (PECVD) method.

European Patent 0 272 143 A2 to Jerry Yuen Kul Wong et al., "Bromine and Iodine Etch Process for Silicon and Silicides," discloses a process for etching single crystal silicon, polysilicon, silicide and polycide using iodinate or brominate gas chemistry.

Sincerely,

A handwritten signature in black ink, appearing to read "S.B. Ackerman", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761



CS-99-065CCB

January 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/694,413 10/27/03 |
Paul Kwok Keung Ho et al.
PLASMA ETCH METHOD FOR FORMING
PLASMA ETCHED SILICON LAYER
| _____ |

ASSOCIATE POWER OF ATTORNEY

I hereby appoint Stephen G. Stanton, registration number 35,690, as my associate attorney in this case. His telephone number is (610) 296-5194.

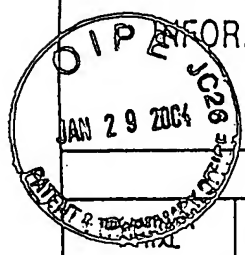
Please continue to direct all correspondence in this case to the undersigned attorney.

Respectfully submitted,

Stephen B. Ackerman,

Principal attorney of record

Form PTO-1449	Document Number (Optional)	Application Number
	CS-99-065 CCB	10/694,413
	Applicant Paul Kwok Keung Ho et al.	
	Filing Date	Group Art Unit
	10/27/03	



(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
5431772	7/11/95	Babie et al.	156	643.1	10/19/92
5456796	10/10/95	Gupta et al.	156	643.1	6/2/93
5681424	10/28/97	Saito et al.	156	643.1	5/20/94
5705080	1/6/98	Leung et al.	216	67	7/6/94
5811356	9/22/98	Murugesesh et al.	438	711	8/19/96
5824375	10/20/98	Gupta	427	569	10/24/96

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
					YES NO
0272143	18/12/87	European Patent App	H01L	21/306	

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.